

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	wafer with (monocrystalline) with (semiconductor or semiconducting) with buried	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 19:27
L2	200	buried adj cavity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 19:27
L3	36	(buried adj cavity) with (insulating or oxide or teos or nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 19:30
L4	8	(buried adj cavity) with (insulating or oxide or teos or nitride) and teos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 19:31
L5	8	(buried adj cavity) with (insulating or oxide or teos or nitride) and teos and oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 19:31
L6	7	(buried adj cavity) with (insulating or oxide or teos or nitride) and teos and oxide and nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 19:31

L7	126	(US-20010023094-\$ or US-20010038886-\$ or US-20010049200-\$ or US-20020072206-\$ or US-20020086551-\$ or US-20020168812-\$ or US-20020195673-\$ or US-20030030062-\$ or US-20030168711-\$ or US-20040012038-\$ or US-20040106290-\$ or US-20040126985-\$ or US-20040137661-\$ or US-20040163476-\$ or US-20040227207-\$ or US-20040237285-\$ or US-20040248349-\$ or US-20040248376-\$ or US-20040253793-\$ or US-20050032364-\$ or US-20050036791-\$ or US-20050051832-\$).did. or (US-4548670-\$ or US-4569307-\$ or US-4660275-\$ or US-4945769-\$ or US-4993143-\$ or US-5153813-\$ or US-5308793-\$ or US-5343064-\$ or US-5386142-\$ or US-5386623-\$ or US-5420953-\$ or US-5448111-\$ or US-5455445-\$ or US-5462637-\$ or US-5682053-\$ or US-5691237-\$ or US-5721162-\$ or US-5800577-\$ or US-5859466-\$ or US-5874675-\$ or US-5909078-\$ or US-5962949-\$ or US-5977604-\$ or US-5990540-\$ or US-5994816-\$ or US-6023121-\$).did. or (US-6114794-\$ or US-6130482-\$ or US-6137206-\$ or US-6169032-\$ or US-6180985-\$ or US-6208007-\$ or US-6211598-\$ or US-6218762-\$ or US-6220096-\$ or US-6236139-\$ or US-6255757-\$ or US-6274919-\$ or US-6275320-\$ or US-6281054-\$ or US-6291922-\$ or US-6306761-\$ or US-6324748-\$ or US-6376291-\$ or US-6386507-\$ or US-6410361-\$ or US-6451668-\$ or US-6472244-\$ or US-6506658-\$ or US-6518147-\$ or US-6579359-\$ or US-6590313-\$ or US-6596147-\$).did. or (US-6628039-\$ or US-6670257-\$ or US-6693039-\$ or US-6740931-\$ or US-6750153-\$ or US-6787052-\$ or US-6800518-\$ or US-6831000-\$ or US-6833079-\$).did. or (EP-1043770-\$ or EP-1049157-\$ or EP-1073112-\$ or EP-1130631-\$ or WO-20020031893-\$ or WO-3030234-\$ or WO-3034016-\$).did. or	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/16 19:32
Search History 8/16/05 7:47:00 PM Page 2 C:\Documents and Settings\Erin\My Documents\EAST\workspaces\10667113_case.wsp WO-3034016-\$).did. or						

L8	82	I7 and oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 19:32
L9	14	I7 and oxide and teos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 19:32
L10	13	I7 and oxide and teos and nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 19:32
L11	14	(buried adj cavity) and oxide and teos and nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 19:34
L12	14	(buried adj cavity) near5 (oxide or nitride or teos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 19:34
L13	20	(buried adj cavity) near10 (oxide or nitride or teos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 19:34
L14	52	wafer same (buried adj cavity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 19:36
L15	16	wafer same (buried adj cavity) same (oxide or insulating or dielectric or nitride or teos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 19:36